

Silicon PNP Power Transistors

2SB1075

DESCRIPTION

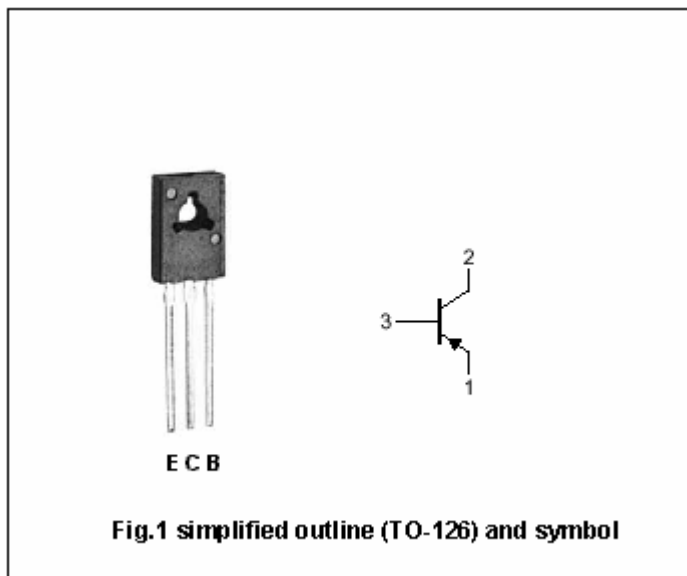
- With TO-126 package
- High collector-peak current
- Low collector saturation voltage

APPLICATIONS

- For audio frequency output amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-40	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-2	A
I_{CM}	Collector current-Peak		-4	A
P_D	Total power dissipation	$T_a=25$	1.2	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-2mA ; I _B =0	-40			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ; I _E =0	-50			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3.0A ; I _B =-0.3A ^{*2}			-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2.0A ; I _B =-0.2A ^{*2}			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V ; I _E =0			-1	μA
I _{CEO}	Collector cut-off current	V _{CE} =-10V ; I _E =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-5V ^{*2}	50		220	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-5V ^{*2}		150		MHz
C _{OB}	Collector output capacitance	I _E =0 ; f=1MHz ; V _{CB} =-20V		40		pF

Note: ^{*2} pulse test◆ h_{FE} Classifications

P	Q	R
50-100	80-160	120-220

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PACKAGE OUTLINE

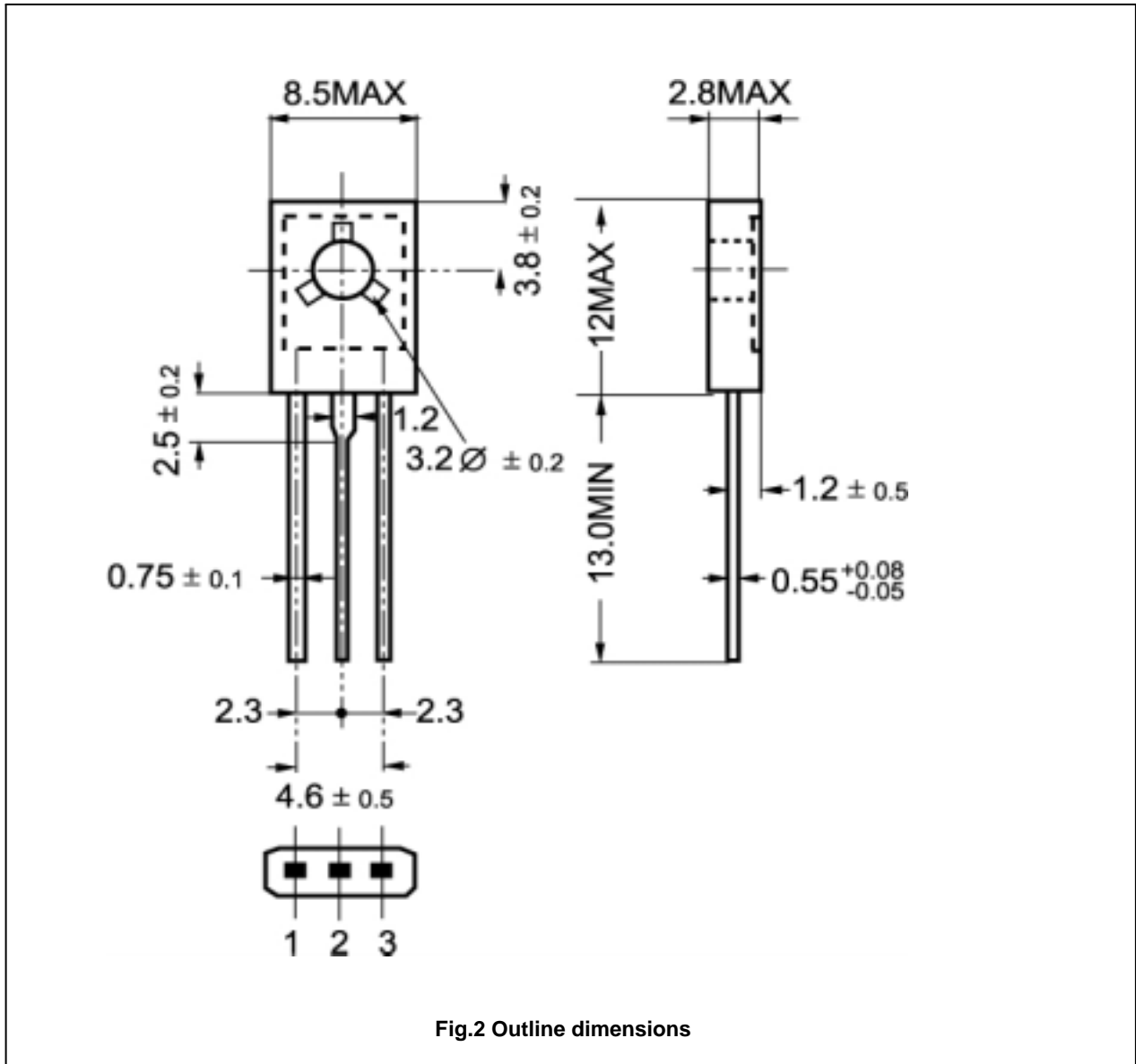


Fig.2 Outline dimensions